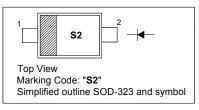
# SILICON SCHOTTKY BARRIER DIODE

for general purpose applications

#### **PINNING**

Γ	PIN	DESCRIPTION
	1	Cathode
	2	Anode



### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit			
Peak Reverse Voltage	$V_{RRM}$	40	V			
Max. Single Cycle Surge Forward Current (10 s Square wave)	I <sub>FSM</sub>	2	Α			
Power Dissipation	P <sub>tot</sub>	400 <sup>1)</sup>	mW			
Junction Temperature	T <sub>j</sub>	200	°C			
Storage Temperature Range	Ts	- 55 to + 200	°C			
1) Valid provided the leads direct at the case are kept at ambient temperature.						

# Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I <sub>R</sub> = 10 μA	V <sub>(BR)R</sub>	40	-	V
Forward Voltage at I <sub>F</sub> = 1 mA at I <sub>F</sub> = 15 mA	V <sub>F</sub>	-	0.39 0.9	V
Leakage Current at V <sub>R</sub> = 30 V	I <sub>R</sub>	-	200	nA
Junction Capacitance at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	C <sub>tot</sub>	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5 \text{ mA}$ , Recover to 0.1 $I_R$	t <sub>rr</sub>	-	1	ns

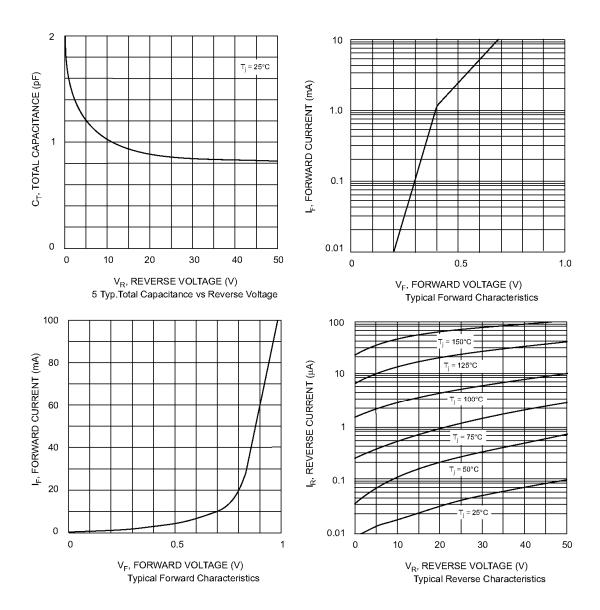








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# **PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-323** 

